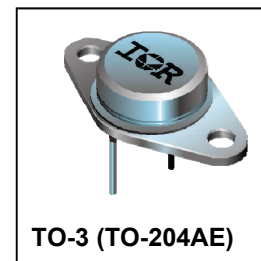


**REPETITIVE AVALANCHE AND  $dv/dt$  RATED  
 HEXFET<sup>®</sup> TRANSISTORS  
 THRU-HOLE -TO-3 (TO-204AE)**
**100V, N-CHANNEL**  
**REF: MIL-PRF-19500/543**
**Product Summary**

Part Number	$BV_{DSS}$	$R_{DS(on)}$	$I_D$
IRF150	100V	0.055 $\Omega$	38A


**Description**

HEXFET<sup>®</sup> MOSFET technology is the key to IR HiRel advanced line of power MOSFET transistors. The efficient geometry and unique processing of this latest “State of the Art” design achieves: very low on-state resistance combined with high trans conductance; superior reverse energy and diode recovery  $dv/dt$  capability.

The HEXFET transistors also feature all of the well established advantages of MOSFETs such as voltage control, very fast switching and temperature stability of the electrical parameters.

They are well suited for applications such as switching power supplies, motor controls, inverters, choppers, audio amplifiers and high energy pulse circuits.

**Features**

- Repetitive Avalanche Ratings
- Dynamic  $dv/dt$  Rating
- Hermetically Sealed
- Simple Drive Requirements
- ESD Rating: Class 3A per MIL-STD-750, Method 1020

**Absolute Maximum Ratings**

Symbol	Parameter	Value	Units
$I_{D1}$ @ $V_{GS} = 10V, T_C = 25^\circ C$	Continuous Drain Current	38	A
$I_{D2}$ @ $V_{GS} = 10V, T_C = 100^\circ C$	Continuous Drain Current	24	
$I_{DM}$ @ $T_C = 25^\circ C$	Pulsed Drain Current ①	152	
$P_D$ @ $T_C = 25^\circ C$	Maximum Power Dissipation	150	W
	Linear Derating Factor	1.2	W/ $^\circ C$
$V_{GS}$	Gate-to-Source Voltage	$\pm 20$	V
$E_{AS}$	Single Pulse Avalanche Energy ②	150	mJ
$I_{AR}$	Avalanche Current ①	38	A
$E_{AR}$	Repetitive Avalanche Energy ①	15	mJ
$dv/dt$	Peak Diode Recovery ③	5.5	V/ns
$T_J$ $T_{STG}$	Operating Junction and Storage Temperature Range	-55 to + 150	$^\circ C$
	Lead Temperature	300 (0.063 in. (1.6mm) from case for 10s)	
	Weight	11.5 (Typical)	

For footnotes refer to the page 2.

**Electrical Characteristics @ T<sub>J</sub> = 25°C (Unless Otherwise Specified)**

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
BV <sub>DSS</sub>	Drain-to-Source Breakdown Voltage	100	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 1.0mA
ΔBV <sub>DSS</sub> /ΔT <sub>J</sub>	Breakdown Voltage Temp. Coefficient	—	0.13	—	V/°C	Reference to 25°C, I <sub>D</sub> = 1.0mA
R <sub>DS(on)</sub>	Static Drain-to-Source On-Resistance	—	—	0.055	Ω	V <sub>GS</sub> = 10V, I <sub>D2</sub> = 24A ④
		—	—	0.065		V <sub>GS</sub> = 10V, I <sub>D1</sub> = 38A ④
V <sub>GS(th)</sub>	Gate Threshold Voltage	2.0	—	4.0	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	—	—	25	μA	V <sub>DS</sub> = 80V, V <sub>GS</sub> = 0V
		—	—	250		V <sub>DS</sub> = 80V, V <sub>GS</sub> = 0V, T <sub>J</sub> = 125°C
I <sub>GSS</sub>	Gate-to-Source Leakage Forward	—	—	100	nA	V <sub>GS</sub> = 20V
	Gate-to-Source Leakage Reverse	—	—	-100		V <sub>GS</sub> = -20V
Q <sub>G</sub>	Total Gate Charge	50	—	125	nC	I <sub>D1</sub> = 38A
Q <sub>GS</sub>	Gate-to-Source Charge	8.0	—	22		V <sub>DS</sub> = 50V
Q <sub>GD</sub>	Gate-to-Drain ('Miller') Charge	25	—	65		V <sub>GS</sub> = 10V
t <sub>d(on)</sub>	Turn-On Delay Time	—	—	35	ns	V <sub>DD</sub> = 50V
t <sub>r</sub>	Rise Time	—	—	190		I <sub>D1</sub> = 38A
t <sub>d(off)</sub>	Turn-Off Delay Time	—	—	170		R <sub>G</sub> = 2.35Ω
t <sub>f</sub>	Fall Time	—	—	130		V <sub>GS</sub> = 10V
L <sub>S</sub> + L <sub>D</sub>	Total Inductance	—	6.1	—	nH	Measured from Drain lead (6mm / 0.25 in from package) to Source lead (6mm / 0.25 in from package)
C <sub>iSS</sub>	Input Capacitance	—	3700	—	pF	V <sub>GS</sub> = 0V
C <sub>oSS</sub>	Output Capacitance	—	1100	—		V <sub>DS</sub> = 25V
C <sub>rSS</sub>	Reverse Transfer Capacitance	—	200	—		f = 1.0MHz

**Source-Drain Diode Ratings and Characteristics**

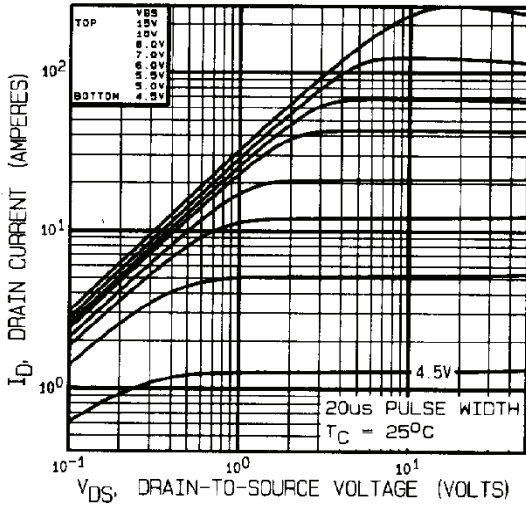
Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
I <sub>S</sub>	Continuous Source Current (Body Diode)	—	—	38	A	
I <sub>SM</sub>	Pulsed Source Current (Body Diode) ①	—	—	152		
V <sub>SD</sub>	Diode Forward Voltage	—	—	1.9	V	T <sub>J</sub> = 25°C, I <sub>S</sub> = 38A, V <sub>GS</sub> = 0V④
t <sub>rr</sub>	Reverse Recovery Time	—	—	500	ns	T <sub>J</sub> = 25°C, I <sub>F</sub> = 38A, V <sub>DD</sub> ≤ 30V
Q <sub>rr</sub>	Reverse Recovery Charge	—	—	2.9	μC	di/dt = 100A/μs ④
t <sub>on</sub>	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L <sub>S</sub> +L <sub>D</sub> )				

**Thermal Resistance**

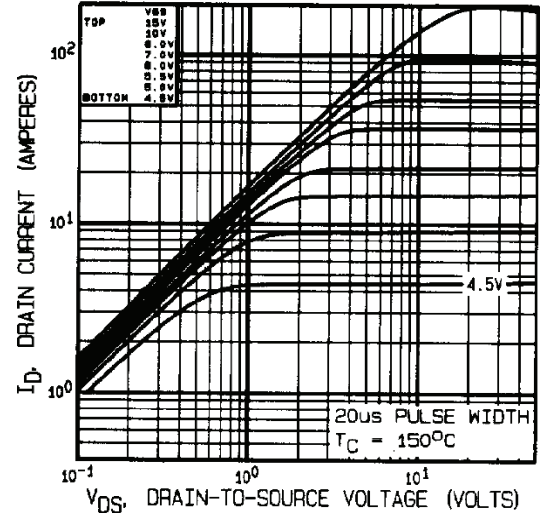
Symbol	Parameter	Min.	Typ.	Max.	Units
R <sub>θJC</sub>	Junction-to-Case	—	—	0.83	°C/W
R <sub>θJA</sub>	Junction-to-Ambient (Typical socket mount)	—	—	30	

**Footnotes:**

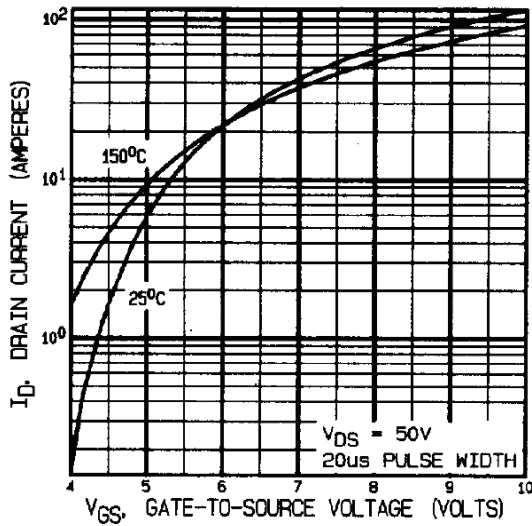
- ① Repetitive Rating; Pulse width limited by maximum junction temperature.
- ② V<sub>DD</sub> = 25V, starting T<sub>J</sub> = 25°C, L = 0.207mH, Peak I<sub>L</sub> = 38A, V<sub>GS</sub> = 10V.
- ③ I<sub>SD</sub> ≤ 38A, di/dt ≤ 300A/μs, V<sub>DD</sub> ≤ 100V, T<sub>J</sub> ≤ 150°C. Suggested R<sub>G</sub> = 2.35Ω
- ④ Pulse width ≤ 300 μs; Duty Cycle ≤ 2%



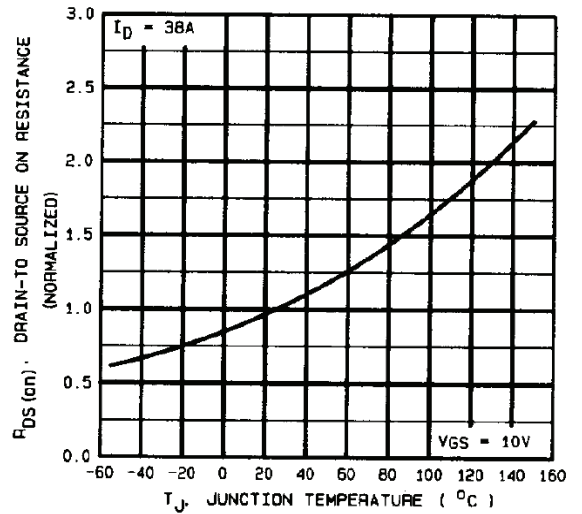
**Fig 1.** Typical Output Characteristics



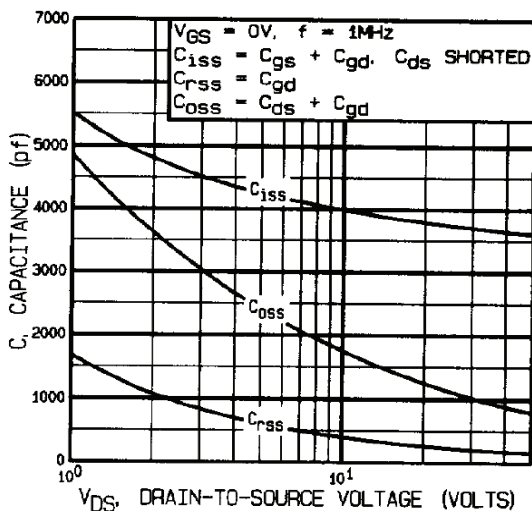
**Fig 2.** Typical Output Characteristics



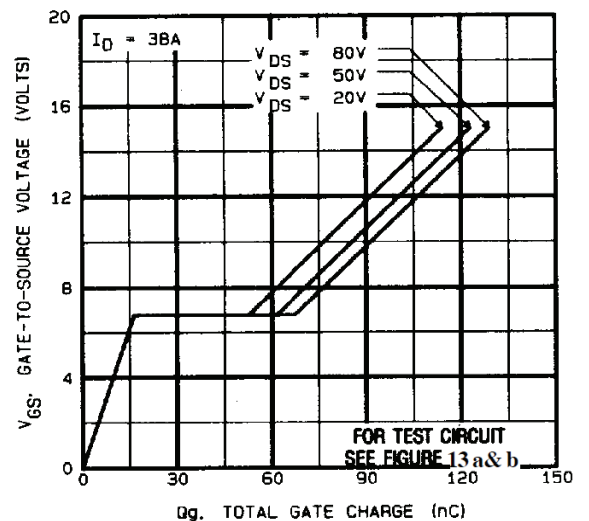
**Fig 3.** Typical Transfer Characteristics



**Fig 4.** Normalized On-Resistance Vs. Temperature



**Fig 5.** Typical Capacitance Vs. Drain-to-Source Voltage



**Fig 6.** Typical Gate Charge Vs. Gate-to-Source Voltage

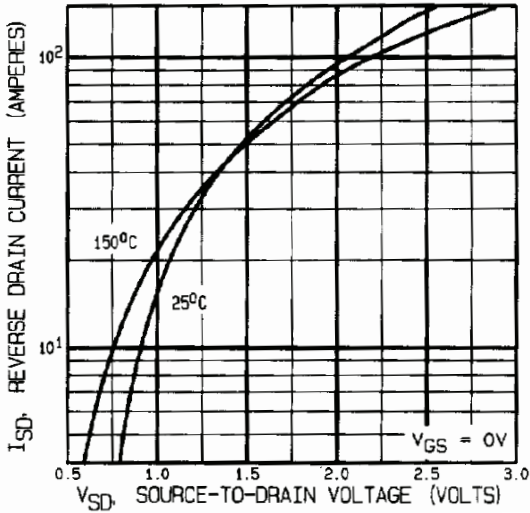


Fig 7. Typical Source-Drain Diode Forward Voltage

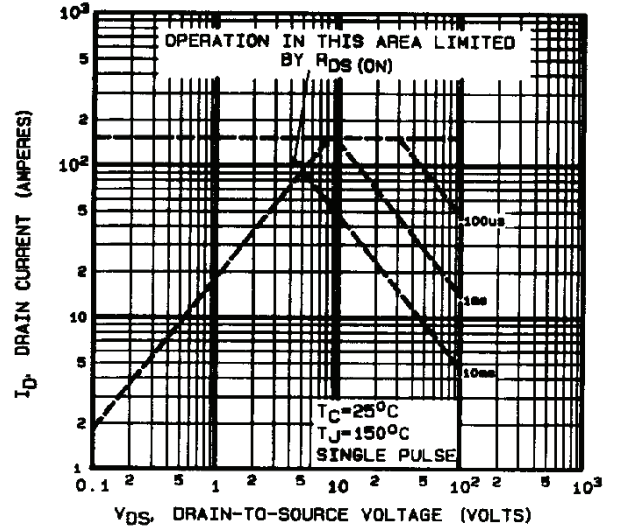


Fig 8. Maximum Safe Operating Area

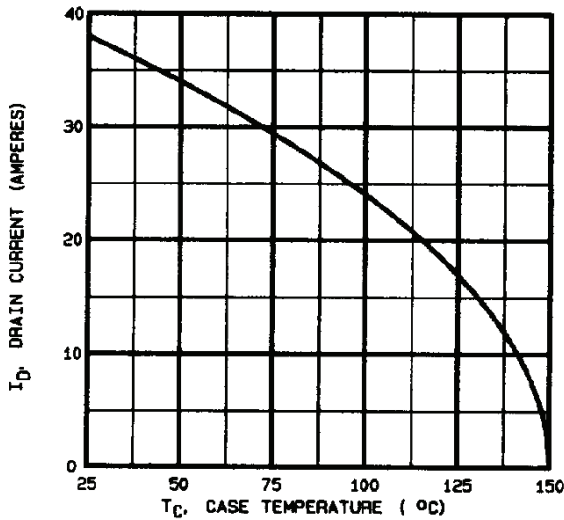


Fig 9. Maximum Drain Current Vs. Case Temperature

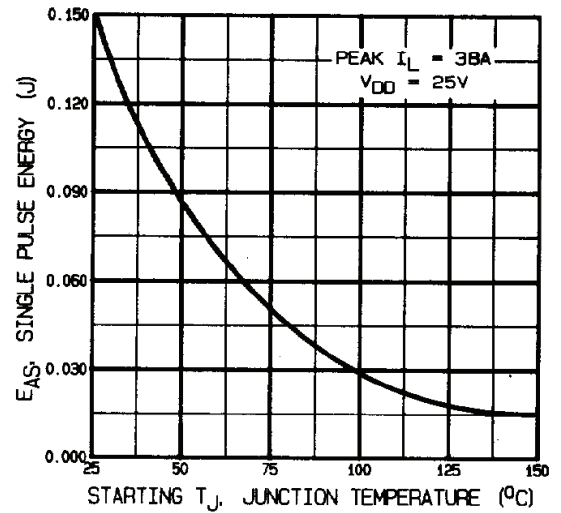


Fig 10. Maximum Avalanche Energy Vs. Drain Current

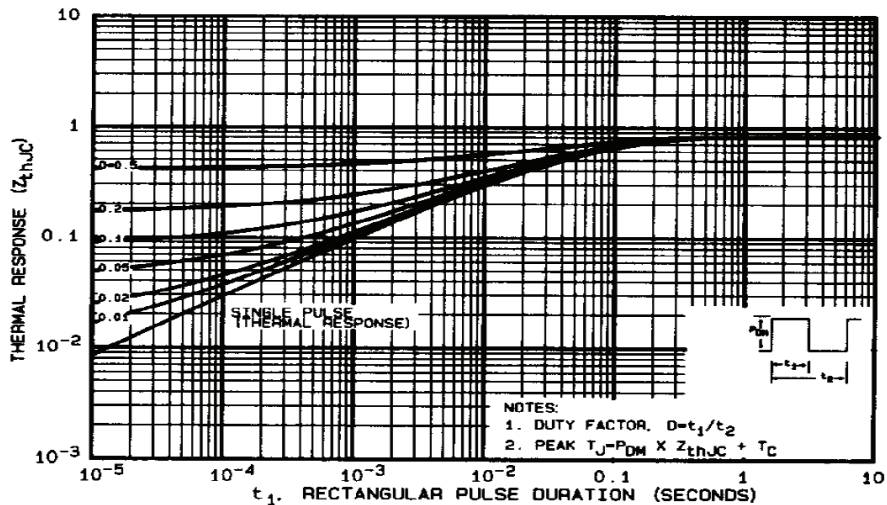
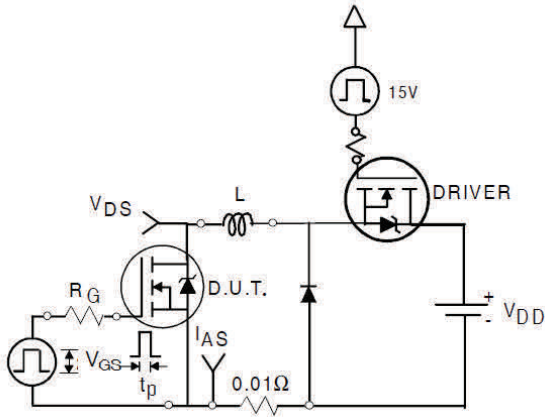
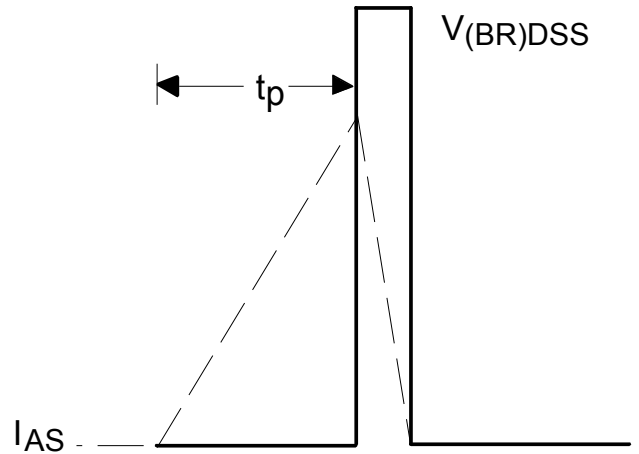


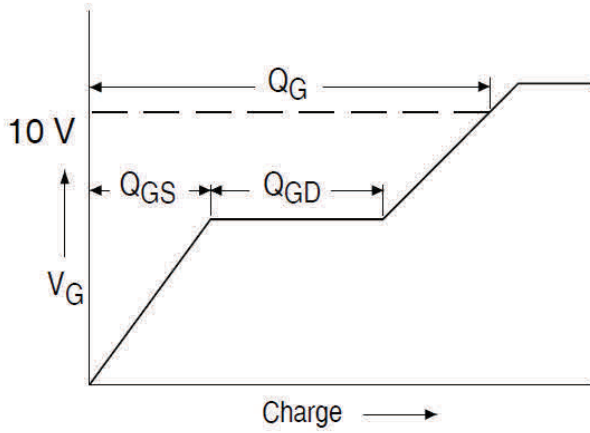
Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case



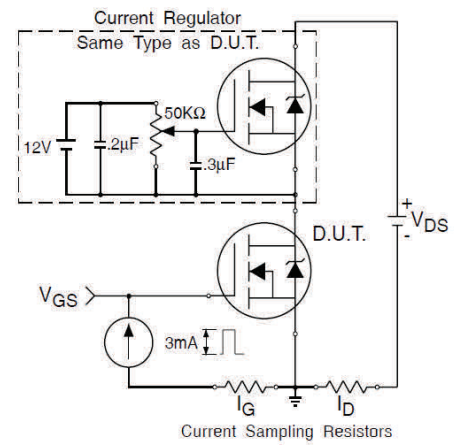
**Fig 12a.** Unclamped Inductive Test Circuit



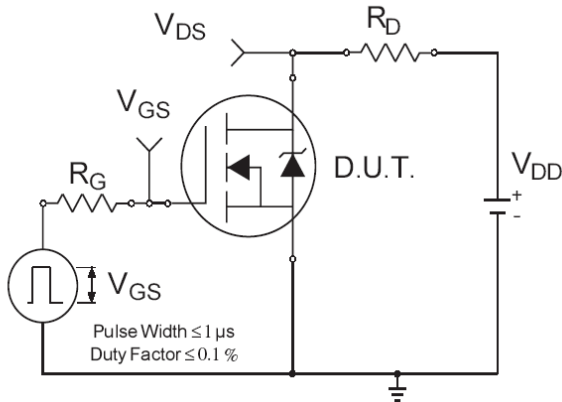
**Fig 12b.** Unclamped Inductive Waveforms



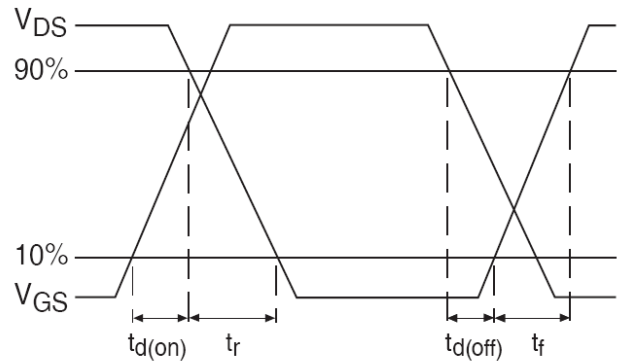
**Fig 13a.** Gate Charge Waveform



**Fig 13b.** Gate Charge Test Circuit

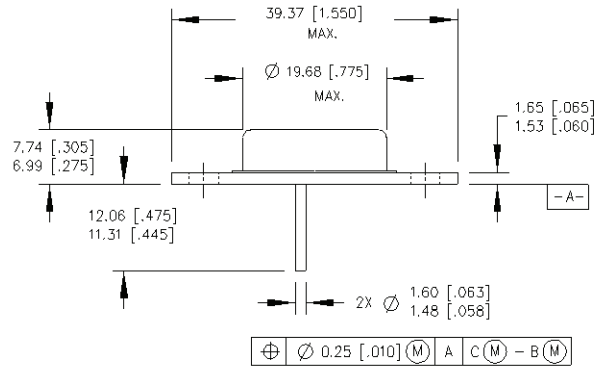


**Fig 14a.** Switching Time Test Circuit



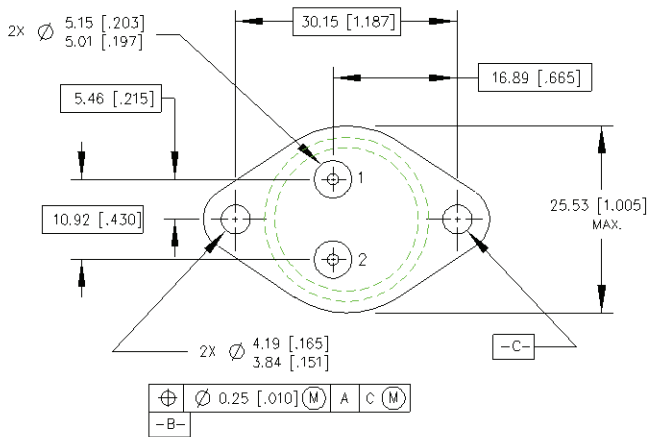
**Fig 14b.** Switching Time Waveforms

**Case Outline and Dimensions - TO-204AE (Modified TO-3)**



**PIN ASSIGNMENTS**

HEXFET	SCHOTTKY	IGBT
1 - SOURCE	1 - ANODE 1	1 - GATE
2 - GATE	2 - ANODE 2	2 - EMITTER
3 - DRAIN (CASE)	3 - COMMON CATHOD (CASE)	3 - COLLECTOR (CASE)



- NOTES:  
 1. DIMENSIONING & TOLERANCING PER ANSI Y14.5M -1982.  
 2. CONTROLLING DIMENSION : INCH.  
 3. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].  
 4. OUTLINE CONFORMS TO JEDEC OUTLINE TO -204-AE.

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